MUR6060PT

Rev.E Mar.-2016

/ Descriptions

TO-3P

Ultrafast Recovery Diode in a TO-3P Plastic Package.

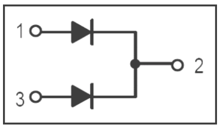
/ Features

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

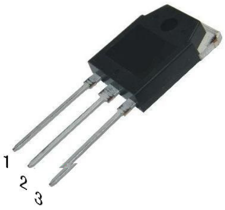
/ Applications

For high frequency, high voltage, high current rectifier diode, freewheeling diode

/ Equivalent Circuit



/ Pinning



PIN1	Anode	PIN2	Cathode	PIN 3	Anode

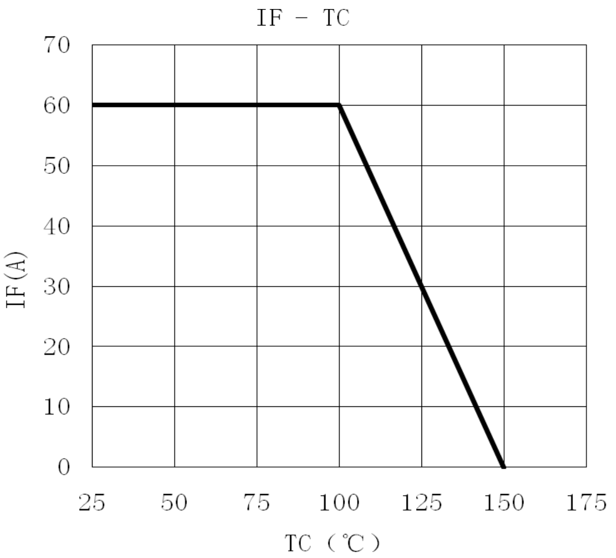
/ h_{FE} Classifications & Marking

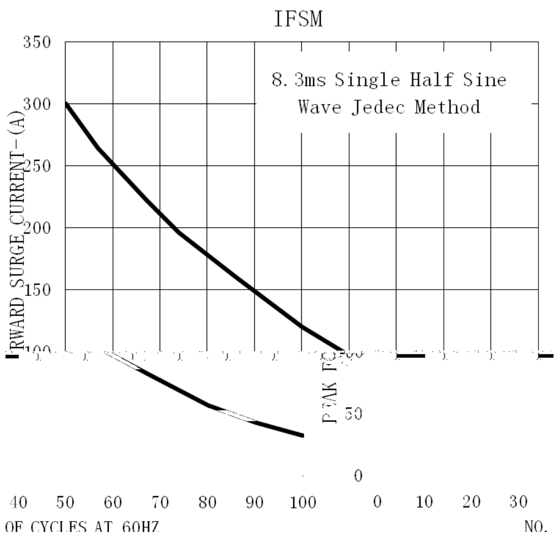
See Marking Instructions

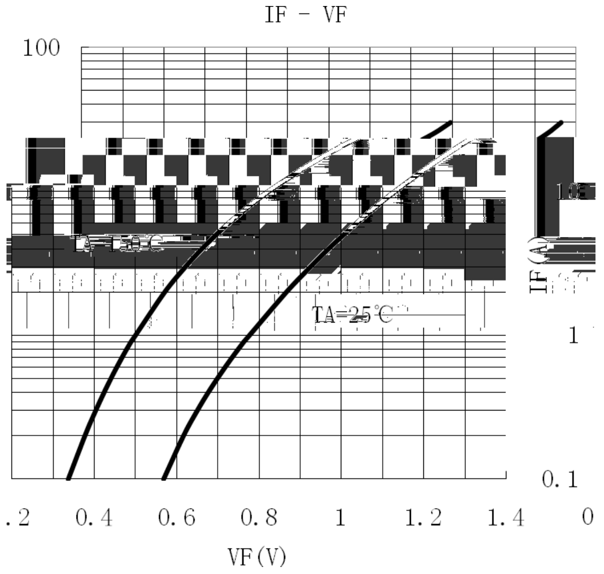
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
RMS Reverse Voltage	V_{RMS}	420	V
DC Blocking Voltage	V_{DC}	600	V
Average Forward Current	I_F	2 30	A
Peak forward surge current	I_{FSM}	300	A
Typical Thermal Resistance Junction to Case	$R_{\theta Jc}$	1.4	/W
Junction Temperature Range	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

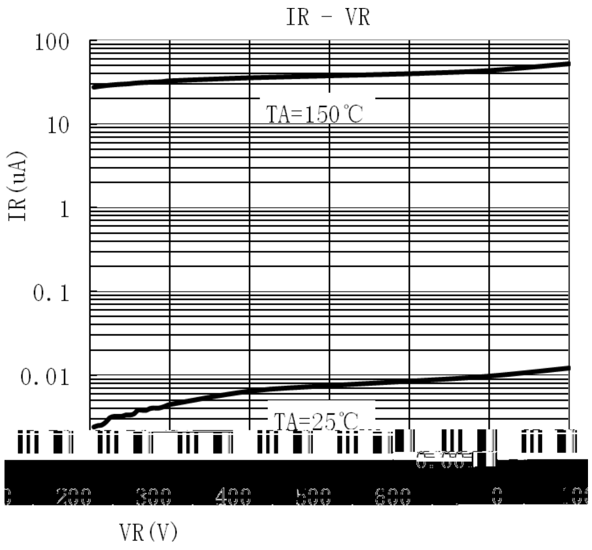
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	I_R=1mA	600			V
		I_F=5A T_C=25			1.35	
Forward Voltage	V_F	0 CFCFC				V y[illegible]

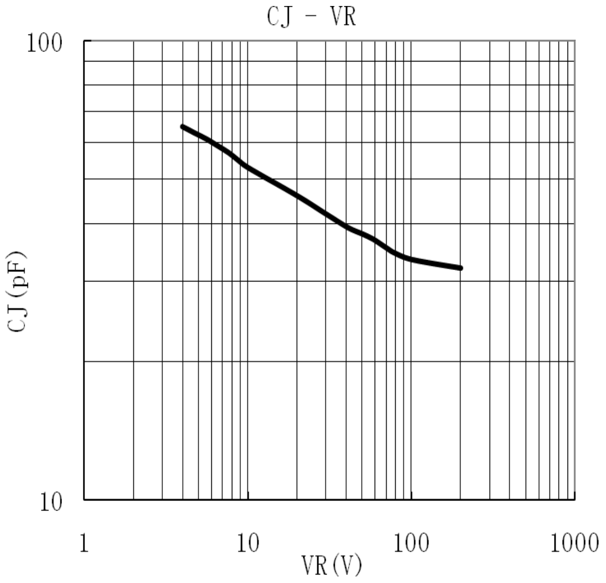
/ Electrical Characteristic Curve



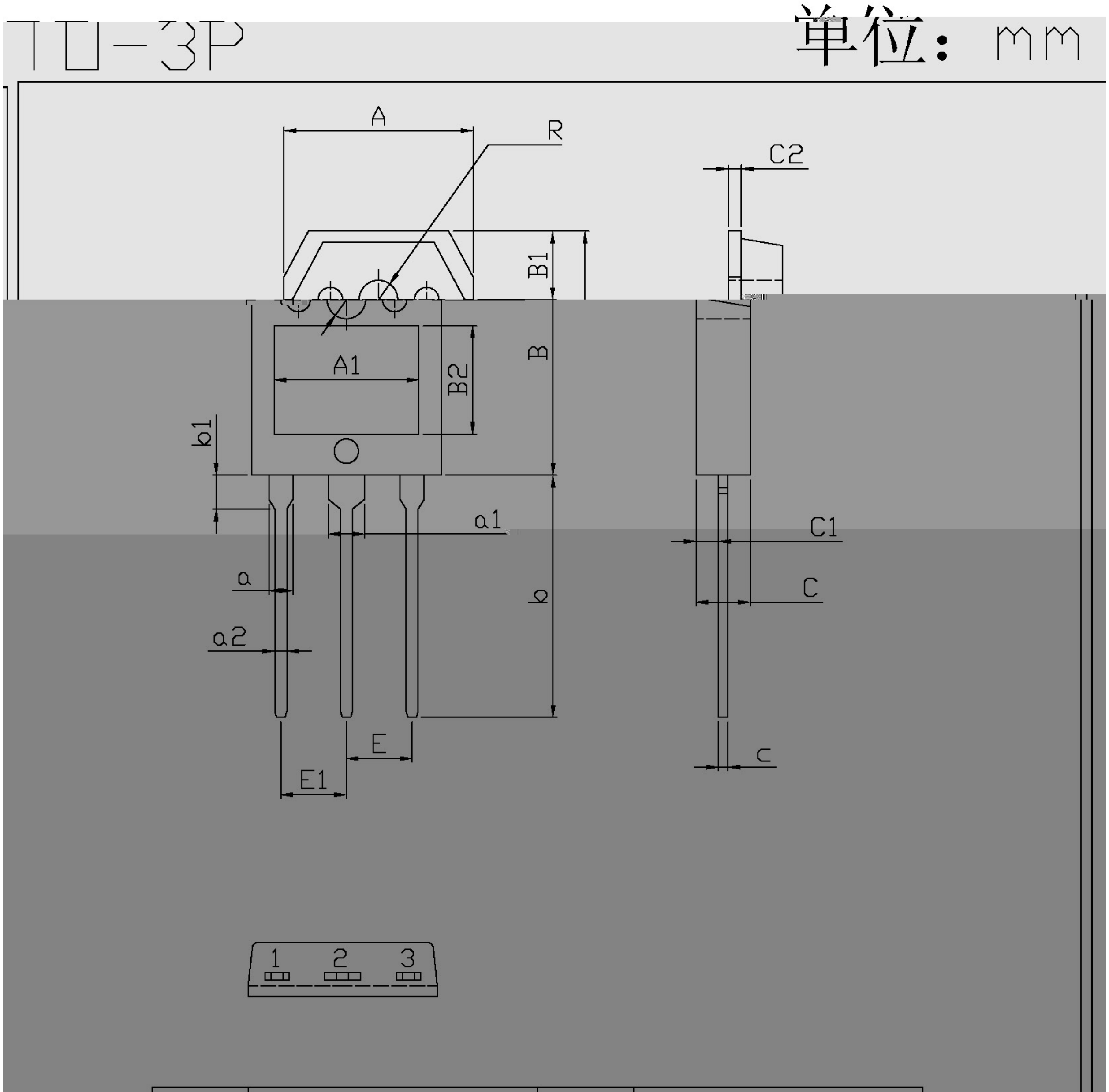








/ Package Dimensions



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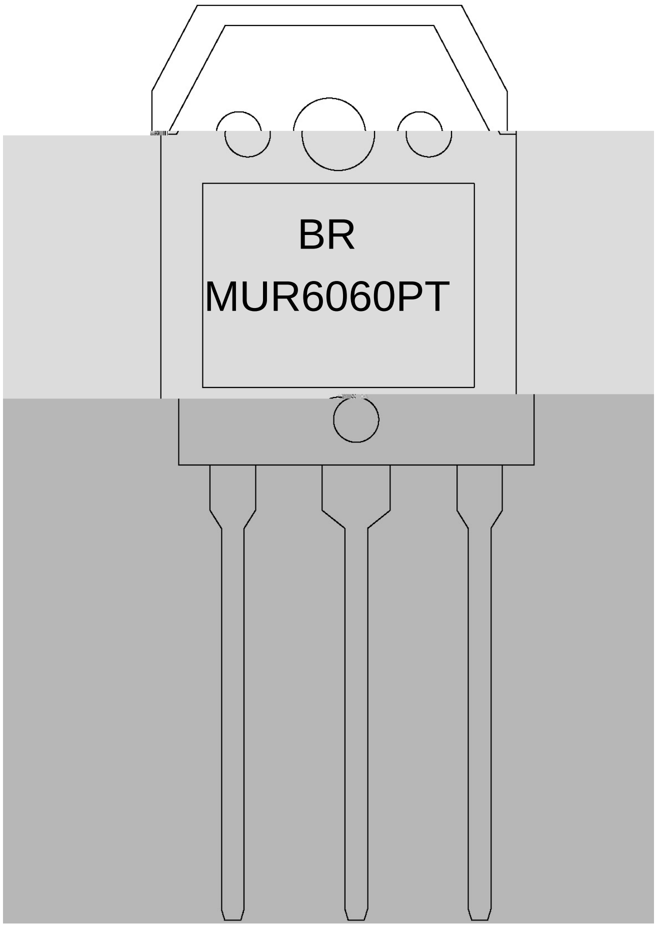
/ Marking Instructions



BR

MUR6060PT

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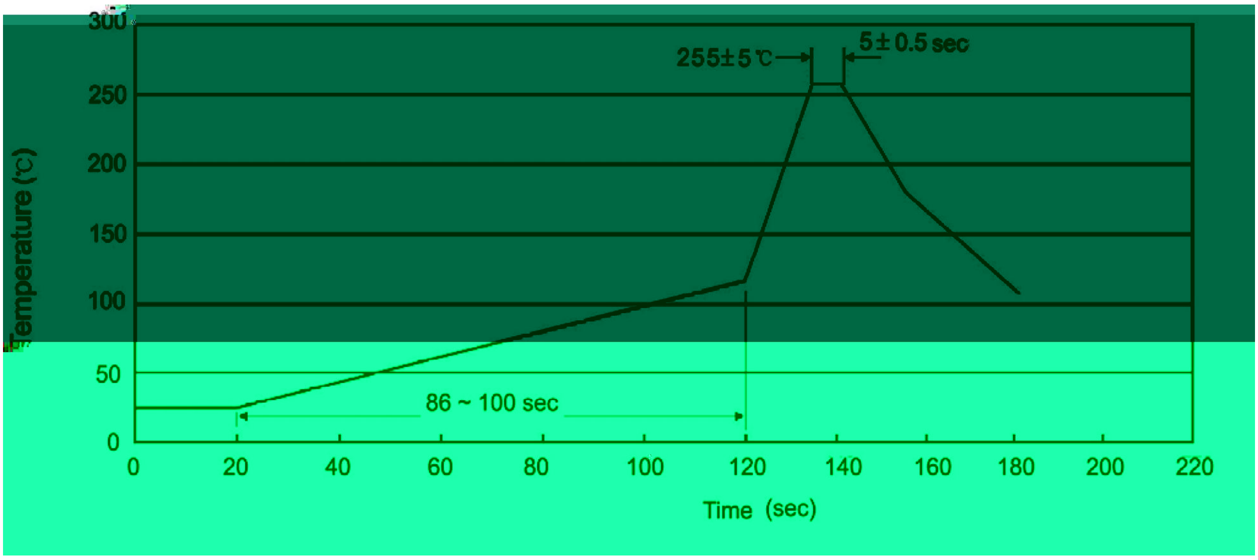
Note:

BR:	Company Code
MUR6060PT	Product Type.
****:	Lot No. Code, code change with Lot No.

(   ) / Temperature Profile for Dip Soldering(Pb-Free)



	Note:
1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 255±5 5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	只 套管	套管 盒	只 盒	盒 箱	只 箱	套管	盒	箱
								× ×

/ Notices